

ABSTRACT OF THE DISCLOSURE

A first on-wafer intended pattern and first and second on-wafer alignment marks have been formed in a reference layer that has been formed on a wafer by using a reference-layer-defining photomask. The first on-wafer intended pattern is a part of an isolation film pattern. The first on-wafer alignment mark has the same width and space as those of the first on-wafer intended pattern. The second on-wafer alignment mark has the same width and space as those of a second intended pattern for a layer-to-be-aligned to be formed on the reference layer. A shift Δx is caused between the first and second on-wafer alignment marks because the diffraction of light affects rough and fine patterns on the photomask differently. In performing alignment by reference to the first alignment mark, the position of a mask to be aligned is corrected by the shift Δx .